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(54) **MOSFET DEVICE AND FABRICATION**

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(57) **ABSTRACT**

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A semiconductor device includes a substrate, an active gate trench in the substrate; a source polysilicon pickup trench in the substrate; a polysilicon electrode disposed in the source polysilicon pickup trench; and a body region in the substrate. The top surface of the polysilicon electrode is below the bottom of the body region.

Related U.S. Application Data

(60) Continuation of application No. 13/456,406, filed on Apr. 26, 2012, now Pat. No. 8,564,055, which is a

